

Low switching losses
 Low reverse recovery charge
 High power cycling capability

Fast Recovery Diode Type DF153-1000-12

Average forward current	I_{FAV}	1000 A
Repetitive peak reverse voltage	V_{RRM}	1000 ÷ 1200 V
Reverse recovery time	t_{rr}	2.5 μ s
V_{RRM} , V	1000	1200
Voltage code	10	12
T_j , °C	- 60 ÷ 125	

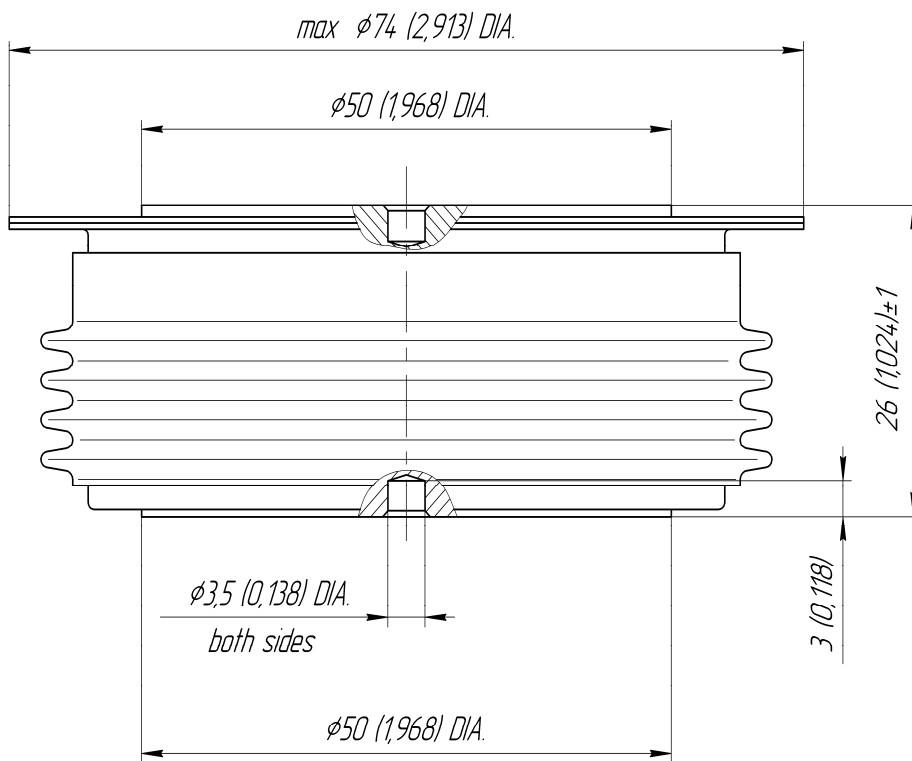
MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{FAV}	Average forward current	A	1000 1875	$T_c=95$ °C; Double side cooled; $T_c=55$ °C; Double side cooled; 180° half-sine wave; 50 Hz
I_{FRMS}	RMS forward current	A	1570	$T_c=95$ °C; Double side cooled; 180° half-sine wave; 50 Hz
I_{FSM}	Surge forward current	kA	29.0 33.0	$T_j=T_{j\ max}$ $T_j=25$ °C 180° half-sine wave; 50 Hz ($t_p=10$ ms); single pulse; $V_R=0$ V;
			31.0 36.0	$T_j=T_{j\ max}$ $T_j=25$ °C 180° half-sine wave; 60 Hz ($t_p=8.3$ ms); single pulse; $V_R=0$ V;
I^2t	Safety factor	$A^2s \cdot 10^3$	4205 5445	$T_j=T_{j\ max}$ $T_j=25$ °C 180° half-sine wave; 50 Hz ($t_p=10$ ms); single pulse; $V_R=0$ V;
			3985 5375	$T_j=T_{j\ max}$ $T_j=25$ °C 180° half-sine wave; 60 Hz ($t_p=8.3$ ms); single pulse; $V_R=0$ V;
BLOCKING				
V_{RRM}	Repetitive peak reverse voltages	V	1000÷1200	$T_{j\ min} < T_j < T_{j\ max}$; 180° half-sine wave; 50 Hz;
V_{RSM}	Non-repetitive peak reverse voltages	V	1100÷1300	$T_{j\ min} < T_j < T_{j\ max}$; 180° half-sine wave; 50 Hz; single pulse;
V_R	Reverse continuous voltages	V	$0.75 \cdot V_{RRM}$	$T_j=T_{j\ max}$;
THERMAL				
T_{stg}	Storage temperature	°C	- 60 ÷ 125	
T_j	Operating junction temperature	°C	- 60 ÷ 125	
MECHANICAL				
F	Mounting force	kN	24.0 ÷ 28.0	
a	Acceleration	m/s^2	50	Device unclamped
			100	Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.90	$T_j=25\text{ }^\circ\text{C}; I_{FM}=3140\text{ A}$	
$V_{F(TO)}$	Forward threshold voltage, max	V	1.15	$T_j=T_{j\text{ max}};$	
r_T	Forward slope resistance, max	$m\Omega$	0.200	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$	
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	150	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$	
SWITCHING					
Q_{rr}	Total recovered charge, max	μC	160	$T_j=T_{j\text{ max}}; I_{FM}=I_{FAV};$	
t_{rr}	Reverse recovery time, max	μs	2.5	$di_R/dt=-100\text{ A}/\mu\text{s};$	
I_{rrM}	Peak reverse recovery current, max	A	128	$V_R=100\text{ V};$	
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	$^\circ\text{C}/\text{W}$	0.0180	Direct current	Double side cooled
R_{thjc-A}			0.0396		Anode side cooled
R_{thjc-K}			0.0324		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	$^\circ\text{C}/\text{W}$	0.0040	Direct current	
MECHANICAL					
w	Weight, typ	g	510		
D_s	Surface creepage distance	mm (inch)	38.84 (1.529)		
D_a	Air strike distance	mm (inch)	22.50 (0.886)		

PART NUMBERING GUIDE						GROUP OF RECOVERY TIME	
DF	153	1000	12	M4	N	Group Symbol	M4
1	2	3	4	5	6	$t_{rr}, \mu\text{s}$	2.5
1. Fast recovery diode 2. Design version 3. Average forward current, A 4. Voltage code 5. Group of reverse recovery time 6. Ambient conditions: N – normal; T – tropical							



All dimensions in millimeters (inches)